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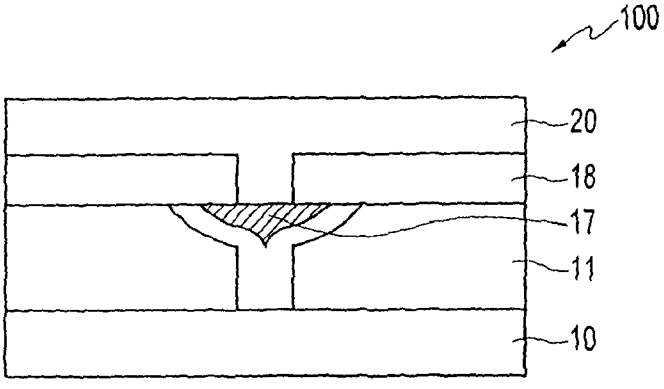


FIG. 9

(57) Abstract: An inverted variable resistance memory cell and a method of fabricating the same. The memory cell is fabricated by forming an opening in an insulating layer deposited over a semiconductor substrate, etching the top portion of the opening to have a substantially hemispherical-shape, forming a metal layer in the opening, and overlying a variable resistance material over the metal layer.

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